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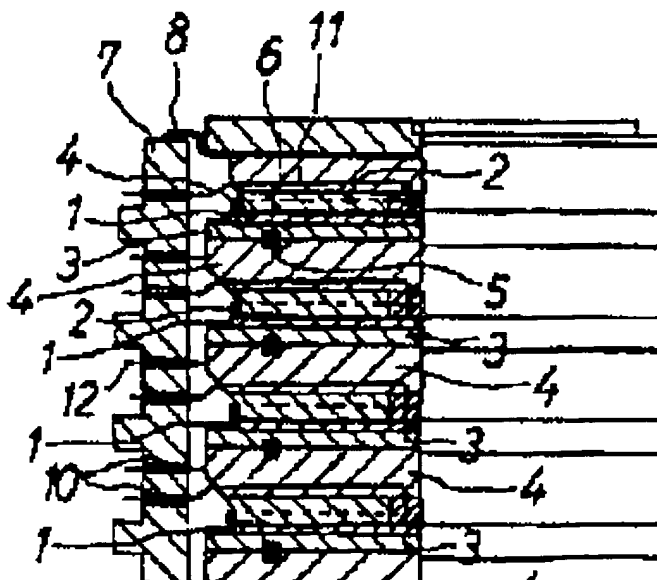
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(54) POWER SEMICONDUCTOR DEVICE

(57) Abstract:

PURPOSE: To prevent positional deviation between stages in a power semiconductor device of multiple-layer stack type.

CONSTITUTION: When stacking a semiconductor substrate 1 in multiple layers along with thermal buffer portions 2 and 3 and an electrode portion 4 which are fixed on the upper and lower surfaces, a pin for preventing rotation 6 is provided at positive pole side thermal buffer portion 3 and then a hole 5 is provided at an electrode portion 4 at the lower-stage side for preventing rotation, thus preventing positional deviation between layers for eliminating troubles such as positional deviation of terminals, the nonuniformity of stage distribution



nonuniformity of stress distribution,
and the instability of electrical
characteristics.

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